

Abstract of the Disclosure:

In an integrated circuit configuration, above a first  
conductive structure which is embedded in a first insulating  
layer there are arranged a first barrier layer and a second  
5 insulating layer, in which a contact hole is provided which  
reaches down to the first conductive structure. Above the  
first barrier layer, the side walls of the contact hole are  
provided with spacers which act as a diffusion barrier and  
which reach down to the surface of the first barrier layer. A  
10 second conductive structure is arranged in the contact hole.  
The second conductive structure is conductively connected to  
the first conductive structure. During the production of the  
contact hole, the spacers prevent deposition of material from  
the first conductive structure on the surface of the second  
15 insulating layer.